

In the Claims

Claims 1-15 (Canceled).

16 (Currently Amended). A device comprising:

a semiconductor substrate having at least one layer with conductive metal lines thereon; and

a dielectric material between the metal lines, said dielectric material having a surface abutting a conductive metal line, the conductive metal line lines having a smoother sidewall than the facing dielectric surface ~~smooth sidewalls adjacent the dielectric material.~~

17 (Original). The device of claim 16 wherein the dielectric material is at least 50% porous.

18 (Original). The device of claim 16 wherein the dielectric material is over a conductive layer.

19 (Original). The device of claim 16 wherein the dielectric material comprises a carbon-doped oxide.

20 (Original). The device of claim 16 wherein the dielectric material has a dielectric constant below about 3.0.

21 (Original). The device of claim 16 wherein the dielectric material comprises fluorinated silica glass.

22 (Original). The device of claim 16 wherein the dielectric material is a silsesquioxane-based material.

23 (Original). The device of claim 16 wherein the dielectric material has a thermal stability greater than about 400 degrees C.